Properties of La-silicate high-K dielectric films formed by oxidation of La on silicon

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(Received 31 July 2002; accepted 31 October 2001)

In this article, we present data on the properties of La-based high-k dielectric films prepared by oxidation of La deposited by physical vapor deposition on silicon. Films are characterized by x-ray photoelectron spectroscopy, infrared absorption, and capacitance versus voltage analysis. We find that when we oxidize La metal sputter deposited on Si substrates, it reacts with the silicon substrate to form La silicate. La films as thick as 300 Å will react completely with Si under moderate oxidation conditions (900 °C for 10 min) suggesting a very rapid silicidation reaction between La and Si. Under some processing conditions the as-deposited films contain a small La2O3 component that reduces to La silicate upon annealing at high temperatures. La-silicate films do not phase separate into La2O3 and SiO2 upon annealing at 1050 °C, and their resistance to H2O incorporation depends critically on the oxidation temperature. Electrical measurements show a high concentration of positive fixed charge. © 2003 American Institute of Physics. [DOI: 10.1063/1.1531818]

I. INTRODUCTION

Continuing miniaturization of the complimentary metal oxide semiconductor (CMOS) devices has resulted in the need for a new higher dielectric constant material to replace SiO2 as the gate dielectric.1 Several such high-k materials, mainly oxides and silicates of group III and IV metals, are currently under investigation.2,3 Most of the attention has focused on materials that are reported to be stable in contact with silicon.4 These thermodynamic calculations apply strictly to the metal oxide and silicon in contact at equilibrium conditions. In reality, physical and chemical deposition processes are inherently nonequilibrium and involve many potential reactions that are not taken into account by purely thermodynamic considerations. Interaction between deposition precursors, reaction intermediates, and/or the substrate can lead to the formation of interfacial layers, which may be SiO2, a silicate, or both. For dielectrics derived from Y, a group III metal, it has been found that a rapid silicidation reaction competes with the oxidation process and leads to the formation of multiple layer stacks consisting of SiO2/YSiO/Y2O3 in both physical vapor deposition (PVD)5 and chemical-vapor deposition6 dielectrics. The oxide of La, another group III metal, is predicted to be stable in contact with Si. However, several recent studies report preferential formation of La-silicate materials over the oxide due to a very efficient mechanism for Si diffusion in La metal and/or La oxide.7,8 In this article, we report the composition, stability, and electrical properties of La-based high-k materials prepared by oxidation of thin La films sputter deposited on Si surfaces. We study the effect of substrate pretreatment on La and Si reactivity and, additionally, we investigate the role of the oxidation temperature on the film’s propensity to absorb H2O from the ambient.

II. EXPERIMENT

We have prepared La-based high-k films by plasma assisted dc sputtering of La metal on H-terminated Si (100) substrates and ex situ furnace oxidation in the presence of N2O as described by Chambers and Parsons and Chambers et al.5,9 The H-terminated Si (100) substrates were prepared by a J T Baker 100 Clean dip for 5 min, deionized water rinse for 5 min, and buffered oxide etch dip for 1 min. They were subsequently blown dry with dry nitrogen and placed in the loadlock of the deposition system. Nitried Si substrates were prepared by in situ exposure of the H-terminated Si to N2 plasma at 300 °C and 50 mTorr for 20 min. This procedure results in ~10 Å of nitride.

The La metal target was purchased from ESPI metals (Ashland, Oregon) and was 99.9% pure. The films described in Sec. III C were deposited in a different PVD system equipped with magnetron sputtering and a La target from Target Materials (Columbus, Ohio) with a purity of 99.9%; oxidation was performed in dry air in a rapid thermal annealing (RTA) furnace.

Metal film thickness was calculated from a calibration curve obtained by ex situ step height measurements performed with a Tencor S profilometer. Steps were prepared by partially covering Si substrates with a glass slide during deposition. This calibration should be regarded as an upper limit to the metal film thickness since La undergoes oxidation when exposed to moisture and oxygen. Films exposed to air for over a day gained significant (at least 50%) thickness indicating that they were only partially oxidized during the initial step height measurements.

Characterization of the film composition was performed by x-ray photoelectron spectroscopy (XPS) and infrared spectroscopy (IR). A Riber LAS3000 instrument equipped with a single-pass, cylindrical mirror (MAC2) analyzer and a Mg Ka (hν = 1253.6 eV), nonmonochromatic x-ray source
was used at a 75° takeoff angle with 0.1 eV step size to obtain the XP spectra. Charge compensation was performed by setting the adventitious C 1s peak to a binding energy of 286.0 eV. Fourier-transform infrared (FTIR) transmission spectra were obtained using a Magna-IR System 750 from ThermoNicolet (Madison, Wisconsin). All spectra were corrected by subtracting the FTIR spectrum of a plain Si substrate. High-resistivity, double-polished Si substrates were used for that part of the study.

Metal-insulator-semiconductor (MIS) capacitors were fabricated via shadow mask deposition of evaporated Al (200 Å). The electrical properties of the films were investigated by capacitance versus voltage (C-V) measurements using an HP4284 LCR. All C-V measurements, unless otherwise stated, were performed at a frequency of 1 MHz and scanned from depletion to accumulation. A Nikon Eclipse Optical Microscope equipped with a digital camera was used to photograph selected capacitors. The digital images were then processed using ImageJ10 to obtain the capacitor area, which was typically $3.5 \times 10^{-4}$ cm$^2$. Capacitors with small areas were selected for the measurements so as to avoid instrumental errors associated with measuring large capacitances. The capacitance versus voltage (C-V) data were analyzed using the ncsu C-V program$^{11}$ to obtain the equivalent oxide thickness (EOT), and flatband voltage.

III. RESULTS AND DISCUSSION

A. Composition of La containing dielectrics formed on clean H-terminated Si (100)

La-metal films with thicknesses from 15 to 330 Å were deposited on H terminated Si (100) substrates and oxidized ex situ at 900 °C in N$_2$O (5 slpm) at atmospheric pressure for times ranging from 30 s to 10 min and equal to the duration of the deposition. X-ray photoelectron spectroscopy was then used to analyze the surface composition (top $\sim 50$ Å) of the films, and the spectral regions containing the Si2p/La4d, O1s, and La3d peaks are displayed on Fig. 1. The thicknesses given correspond to the original thickness of the metal deposited. The resulting dielectric film thickness is approximately twice the original metal thickness. For the thinnest films, we were able to probe the Si- dielectric interface and detect the substrate Si 0 peak$^{12}$ at 99.3 V in the Si2p spectra. The absence of silicide peaks is consistent with the selected oxidation conditions. The spectral region around the Si2p peaks [Fig. 1(a)] also contains contributions from the La4d peaks$^{13}$ at 101.9 and 105.5 eV that overlap with the SiO$_2$ peak expected at 103.3 eV.$^{12}$ No attempts were made to deconvolve the peaks.

For the O1s spectra in Fig. 1(b) we can observe a clear transition from a double to a single peak as the film thickness increases. The shoulder at $\sim 533.0$ eV is clearly visible for the thinnest (15 Å of La metal) film and indicates the presence of a SiO$_2$ interfacial layer.$^{12}$ As the film thickness increases and we lose the ability to probe the interface, the O1s spectra exhibit a single peak at $\sim 531.8$ eV. This peak lies between the SiO$_2$ and La$_2$O$_3$ peaks at 533.3 and 529.9 eV$^{13}$ respectively, consistent with the formation of La–O–Si silicate bonding units. For the thinnest film, the peak position is marginally shifted to a higher-binding energy indicating the presence of a more Si-rich silicate layer close to the interface. The La4d and La3d spectra in Figs. 1(a) and 1(c) are also consistent with the silicate composition for all thicknesses studied. The La3d and La4d features shift slightly to a lower-binding energy as the film thickness increases suggesting a higher-La fraction in the thicker films. However, this shift is very slight with the largest changes occurring between 15 and 25 Å.

The O1s and La3d peak positions remain practically unchanged with film thickness implying that the diffusion of Si atoms into the La metal film proceeds very rapidly at the temperatures studied and the silicidation reaction may proceed at a faster rate than the oxidation. Mixing of La with Si probably occurs even during the metal film deposition at room temperature, and exposure to the oxidizing ambient at high temperature increases the La and Si mobility. These results are consistent with a mechanism in which La silicide is formed, and subsequently as oxidants diffuse through the film it oxidizes to form La silicate, and interfacial SiO$_2$. Such a mechanism is consistent with previous studies$^{14,15}$ that report a fairly rapid intermixing of Si and La layers even at temperatures as low as 150 °C. However, we acknowledge that our results could also be explained by rapid Si diffusion in La$_2$O$_3$films as observed recently both for metal-organic chemical-vapor deposition$^7$ and e-beam evaporated oxide films.$^8$

These findings share some common features with previous observations regarding Y-based films formed in similar manner. Chambers and Parsons$^5$ found that competition between two reactions, silicidation at the bottom of the deposited metal and oxidation at the top, resulted in two regimes.
for growth. For thin Y films, the Si/Y mixing was sufficiently fast to form a single layer having silicate composition as observed in our lanthanum studies. However, a second regime was identified for relatively thicker films (>80 Å) in which competition between silicidation and oxidation resulted in the formation of a SiO₂/YSiO/Y₂O₃ layered structure. This second regime was never identified in our work, and the difference is quite interesting since both Y and La are group III metals and may be expected to have similar chemical properties. An IR study of the interfacial reactions between rare-earth-metal oxides and Si substrates by Ono and Katsumata found that the fraction of silicate bonding increases with the ionic radius of the rare-earth element. Larger atoms, in general, leave more free space for Si diffusion. The extent of silicate formation for PVD Y- and La-based dielectrics corroborates the conclusion that enhanced Si diffusivity in the lanthanum system is a key factor that controls whether the oxide or silicate of the metal is preferentially formed.

B. Effect of substrate on the film composition

We analyzed the composition of thick films (170 Å metal) deposited on various substrates, and results are shown in Fig. 2. Figures 2(a) and 2(b) show O1s and La3d XP spectra, respectively, for the following three films: 170 Å of La metal oxidized at 900 °C for 5 min in N₂O deposited on (i) H-terminated Si (100); (ii) plasma nitrided Si (100); and (iii) 1000 Å of thermal SiO₂. The O1s spectra for samples (i) and (ii) are practically identical and are consistent with La-silicate formation. Sample (iii), formed on 1000 Å thermal SiO₂, shows a primary feature at 531.5 eV and a significantly smaller one at 529.9 eV, indicating that LaO–Si with a small fraction of La₂O₃ bonding are present in the film. The La3d spectrum for sample (iii) is shifted towards the low-binding energies compared to those for samples (i) and (ii), consistent with the presence of La₂O₃ in sample (iii), and with our interpretation of the O1s spectra for this film. The peak broadening may be due to a graded composition in sample (iii).

To gain further insight into the reactions of La metal on thick SiO₂, a very thick La film (1000 Å) was deposited on SiO₂ for comparison with sample (iii). Figure 3 shows XP data for samples formed by depositing 170 Å of La on 1000 Å SiO₂ (sample iii), and 1000 Å La on 1000 Å SiO₂ (sample iv). Film stacks were oxidized at 900 °C for 5 min. The O1s XP spectra show a primary peak at 531.5 eV and a secondary peak at 530 eV consistent with the presence of some La₂O₃ in a mainly silicate film. The thicker La layer results in a more pronounced and narrower La₂O₃ feature. The broadening of the La3d peaks towards the low-binding energies compared with films (i) and (ii) is also consistent with the existence of La₂O₃ in films (iii) and (iv).

We now discuss differences in reactions on plasma nitrided and thermally oxidized substrates. Comparing data from samples (i) and (ii), the presence of an ultra-thin layer of nitrided Si in sample (ii) does not impede significantly the diffusion of Si atoms into the La-metal film. This result is in contrast to that obtained from studies of Y on nitrided Si where the presence of ~10 Å of nitrided Si did impede reaction of Y and Si. The larger ionic radius of the La atom compared to that of Y may account for this difference. It is also conceivable that in both cases, metal nitride layers (La–N or Y–N) are formed at the interface. The lattice constants for La–N is expected to be ~5.3 Å (Ref. 18) which is significantly larger than the 4.88 Å expected for Y–N, thus facilitating the diffusion of the Si atoms through the La–N layer.

The XPS detection of Si near the top of films (iii) and (iv), which were deposited on 1000 Å of thermal SiO₂, shows the remarkable ability of La metal to reduce SiO₂ during thermal treatment likely by breaking Si–O bonds. It was shown above that Si atoms are highly mobile in La and La oxide and diffuse through ~1000 Å of deposited metal to form La–O–Si units at the sample surface. In the case of La–SiO₂ reactivity, the silicidation reaction requires additionally the breaking of fairly strong (4.85 eV) Si–O bonds. As a result, one expects thicker metal films would be more likely to have La₂O₃ at the surface. The data in Fig. 3 supports this idea. The intensity of the La₂O₃ peak in the La3d spectrum is significantly larger for the film prepared from the thicker (1000 Å) original La metal. The O1s peak for sample
reports some silicate formation for La$_2$O$_3$/SiO$_2$/Si structures, demonstrated that reoxidation of a 23 Å LaO$_x$ of more SiO$_2$ in the film as compared to samples towards high-binding energies may be ascribed to the presence at 533.3 eV consistent with a La-rich top layer. 

Corroborate previous observations by Copel et al. annealed at 800 °C. 

And H-terminated Si or nitrided Si substrates in samples subjecting the films to extended thermal treatment at 1050 °C. Thus, we believe that the presence of La$_2$O$_3$ in films (iii) and (iv) is likely due to a slower reaction between La and SiO$_2$, compared to the reaction between La metal and H-terminated Si or nitrided Si substrates in samples (i) and (ii).

The conclusions of this work regarding the ability of La metal to reduce thick layers of SiO$_2$ during thermal treatment corroborate previous observations by Copel et al. who demonstrated that reoxidation of a 23 Å La$_2$O$_3$/20 Å thermal SiO$_2$ structure at 850 °C resulted in the complete reduction of the SiO$_2$ and the formation of La–O–Si. Stemmer et al. also reports some silicate formation for La$_2$O$_3$/SiO$_2$/Si structures, annealed at 800 °C.

C. Thermal stability of La-silicate films

The propensity of the La-silicate films to phase separate into the La$_2$O$_3$ and SiO$_2$ components was investigated by subjecting the films to extended thermal treatment at 1050 °C in a rapid thermal anneal (RTA) instrument in Ar atmosphere. For this purpose, La metal (150 Å) was deposited via magnetron sputtering on H-terminated Si and RTA oxidized ex situ at either 600 or 900 °C in dry air for 5 min. Each dielectric film was cleaved into three pieces and subjected to a different thermal treatment. Sample (v) received no further annealing beyond the oxidation step. Sample (vi) was annealed in Ar at 1050 °C for 10 s, and sample (vii) was annealed at the same temperature for 30 s. Figure 4 shows the O1s XP spectra for samples (v) through (vii) for films oxidized at 900 and 600 °C. With longer annealing time, the O1s peak position shifts marginally towards lower-binding energies, but phase separation is not observed.

Additionally, both 900 and 600 °C as-deposited films exhibit a small La$_2$O$_3$ content as evidenced by the low-binding energy shoulders in the O1s and La3$d$ (not shown) peaks. This oxide is not present in the N$_2$O oxidized films and is probably due to the different oxidation environment or the faster temperature ramp in the RTA instrument than in the conventional furnace used for samples discussed in previous sections. The oxide is reduced to silicate upon thermal anneal, and this silicate exhibits remarkable thermal stability even upon a 30 s thermal excursion at 1050 °C which exceeds the thermal budget currently experienced by the CMOS gate dielectric during dopant activation.

D. Atmospheric H$_2$O absorption of La-silicate films

The hygroscopic nature of the silicate films was investigated by FTIR. Thick La films (330 Å metal) were deposited on high resistivity Si substrates and oxidized for 10 min at either 600 or 900 °C. The IR spectrum of each sample was recorded within 10 min of the oxidation. The films were left in ambient air, and the IR spectrum between 4000 and 400 cm$^{-1}$ was recorded periodically.

Figure 5 shows spectra recorded immediately (within 10 min after oxidation) and after 10 days of ambient exposure...
for films oxidized at 900 °C [Fig. 5(a)] or 600 °C [Fig. 5(b)]. The 900 °C film oxidized exhibits an absorption feature at 1100 cm$^{-1}$ corresponding to the Si–O–Si asymmetric stretch in SiO$_2$. The peak due to the Si–O–Si bending mode located at 810 cm$^{-1}$ is superimposed onto a broader set of peaks located between 780–1020 cm$^{-1}$ and indicative of La-silicate structure. The La$_2$O$_3$ feature at 3440 cm$^{-1}$ could not be investigated due to instrument limitations. The IR spectrum of the film oxidized at 900 °C remains practically unchanged after ten days of air exposure.

The film oxidized at 600 °C exhibits a far richer absorption spectrum. Following oxidation, interfacial SiO$_2$ formation is revealed by the Si–O–Si asymmetric stretching mode at 1100 cm$^{-1}$. The intensity of the silicate peaks between 780–1020 cm$^{-1}$ is significantly reduced while several other peaks appear in the spectrum. Significant reaction with moisture is revealed by the hydroxyl group stretching mode peaks at 3440 cm$^{-1}$ for OH in La(OH)$_3$ and the small shoulder near 3600 cm$^{-1}$ caused by OH in La(OH)$_3$. The broad feature between 1500 and 1300 cm$^{-1}$ suggests the presence of hydrocarbonate phases, La$_2$(OH)$_6$(CO$_3$)$_3$, possibly from reaction with atmospheric H$_2$O and CO$_2$. Infrared spectroscopy has been used previously to observe reactions between atmospheric CO$_2$, moisture, and La$_2$O$_3$ powders and films. After ten days of ambient exposure, the peaks become more intense, and three peaks at 3610, 1580, and 640 cm$^{-1}$ appear in the spectrum. The very strong features at 3610 and 640 cm$^{-1}$ are assigned to the O–H stretching and La–OH bending modes of La(OH)$_3$. The peak at 1580 cm$^{-1}$ is probably due to the formation of another La hydrocarbonate.

The oxidation temperature appears to affect significantly the film’s reactivity with atmospheric components such as moisture and CO$_2$. Rare-earth oxides and La$_2$O$_3$ powders are known to react with atmospheric components. Rosynke and Magnusson demonstrated that prolonged (~40 h) annealing of La hydrocarbonate in vacuum leads to a first stage dehydration at 200 °C and complete dehydration at around 400 °C. The carbonate decomposes between 400 and 800 °C. XPS analysis of films oxidized at 600 and 900 °C and kept in the controlled atmosphere of a dessicator reveals that both materials have similar silicate compositions. Thus, we believe that oxidation at either 600 or 900 °C is sufficient to desorb all the impurities that form within the 1–2 min air exposure prior to oxidation. The oxidation temperature was the only step in the preparation of these samples that was varied. It is likely that oxidation at 900 °C results in a more densely packed film structure than oxidation at 600 °C. A higher porosity would facilitate the diffusion of atmospheric elements in the 600 °C silicate film and allow hydrocarbonate formation within minutes of exposure.

Nieminen et al. have reported IR results for La$_2$O$_3$ films grown on Si. The as-deposited films exhibit La(OH)$_3$ and carbonate features that disappear following a 30 min N$_2$ anneal at 800 °C. However, these reappear and strong La(OH)$_3$ features develop after subsequent exposure to air. The chemical stability exhibited by the 900 °C La silicate in this study is quite remarkable and noteworthy.

E. Electrical measurements on La-silicate films

The electrical properties of the La-silicate films were evaluated by C-V measurements on MIS capacitors with Al gates. No forming gas anneal was performed. Figure 6 shows a representative curve taken at 1 MHz and 100 KHz for 10 Å La metal oxidized at 900 °C for 5 s in N$_2$O. The area of the capacitor was measured at 3.53×10$^{-4}$ cm$^2$ optically. The transition from depletion to accumulation appears to stretch over 1 V. This voltage stretchout is characteristic of the interface trap charge that is uniformly distributed throughout the band gap. Analysis of the 1 MHz curve with the NCSU C-V program that corrects for quantum-mechanical effects yields an equivalent oxide thickness (EOT) of 15.3 Å. The flatband voltage was −1.08 V, shifted by about −1.1 V from its expected position, in agreement with previous findings by Guha et al. and Copel et al. The direction and magnitude of the flatband voltage shift indicates the presence of a fixed charge density of about 1×10$^{11}$ cm$^{-2}$, which is unacceptably high for CMOS technology. The origin of the charge is not yet understood, and no attempt was made to distinguish oxide trapped and interface trapped charge. The gate material is Al and the area of the capacitor is 3.53×10$^{-4}$ cm$^2$.
tion to accumulation and vice versa several times. The displacement of the flatband voltage is \(\sim 20 \text{ mV}\) after the first cycle and reduces to \(\sim 7 \text{ mV}\) for each of the subsequent three cycles. This shift in the \(C-V\) curves under stress indicates another instability in the films, and can be explained by the generation of negative charge in the gate dielectric. Similar observations have been documented for other high-\(k\) materials such as ultrathin \(\text{ZrO}_2\) and \(\text{SiO}_2/\text{ZrO}_2\) films. The magnitude of the hysteresis remains practically unchanged from the first to the fifth cycle, however the observed shift in the flatband voltage under stress is fairly undesirable as it implies a threshold voltage instability when applied to field-effect transistors.

IV. CONCLUSIONS

Thin dielectric films were created by La metal PVD and \textit{ex situ} furnace oxidation in \(\text{N}_2\text{O}\). XPS analysis revealed that regardless of the initial metal thickness the films were a La-silicate material with fairly constant composition. Oxidation at 600 and 900 °C yielded materials of fairly similar silicate composition that did not phase separate into \(\text{La}_2\text{O}_3\) and \(\text{SiO}_2\) even when subjected to inert atmosphere anneals at 1050 °C for 30 s, conditions that exceed the current gate dielectric thermal stability requirements. The oxidation temperature, however, had a severe effect on the chemical stability of the films to air exposure. La-silicate films oxidized at 600 °C were susceptible to La hydrocarbonate and \(\text{LaO(OH)}_3\) formation within minutes of air exposure. Prolonged ambient exposure resulted in the formation of \(\text{La(OH)}_3\). Films oxidized at 900 °C, on the other hand, showed no sign of reaction with moisture or \(\text{CO}_2\) that were within the detection limits of the FTIR instrument. Despite the good properties of these silicate films, large concentrations of a positive fixed charge have been observed. Unless it can be neutralized or somehow reduced, this charge limits the usefulness of La silicate as a replacement for \(\text{SiO}_2\) in CMOS technology.

ACKNOWLEDGMENTS

The authors would like to thank Scott Burnside, Tammi Schmit, and Justin Bennett for assistance with the film deposition and characterization, and Rob Ashcraft and Dong Niu for assistance with the IR and RTA. Financial support from SRC customization funding through LSI Logic Inc., and NSF (Grant No. CTS-0072784) is gratefully acknowledged.


FIG. 7. Hysteresis curves for the capacitor in Fig. 6. The inset shows a magnification of the flatband voltage area. The magnitude is \(\sim 25 \text{ mV}\) without post-metallization anneal.